

FIG. 1A

FORMATION OF AMORPHOUS SEMICONDUCTOR FILM

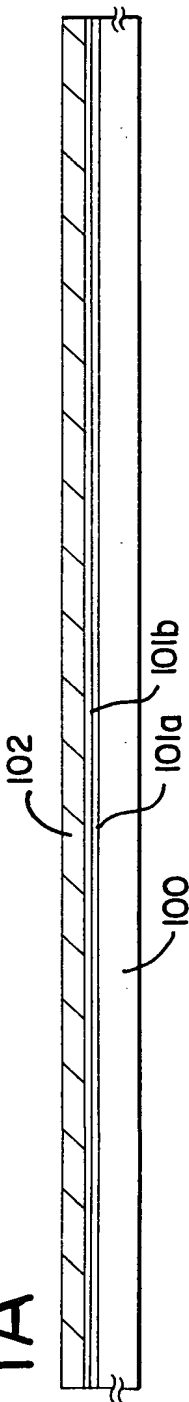


FIG. 1B

FORMATION OF CATALYTIC ELEMENT CONTAINING LAYER

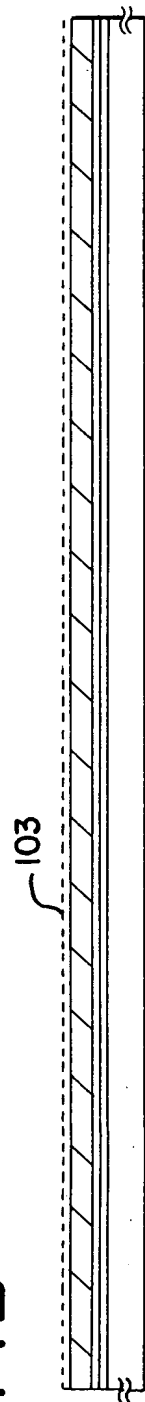


FIG. 1C

HEAT TREATMENT (CRYSTALLIZATION OF SEMICONDUCTOR FILM)

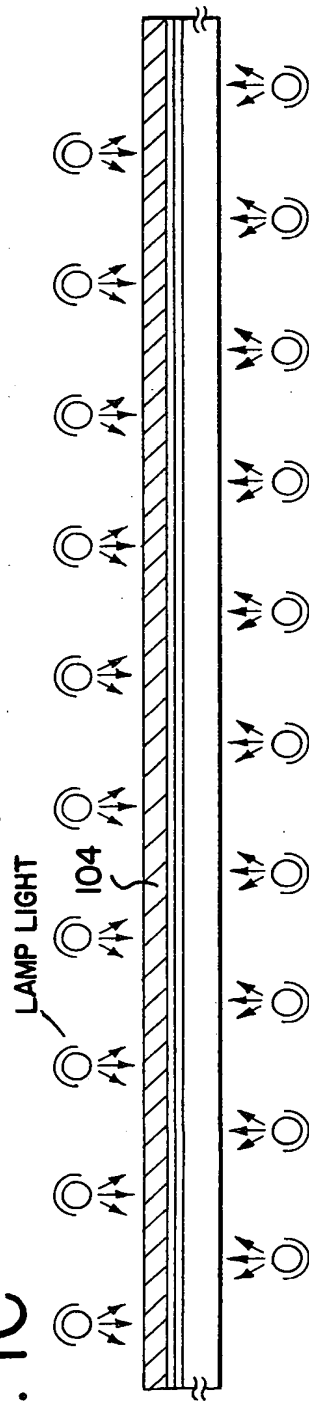
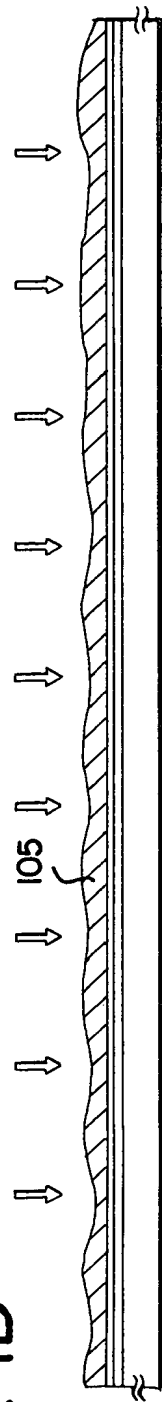


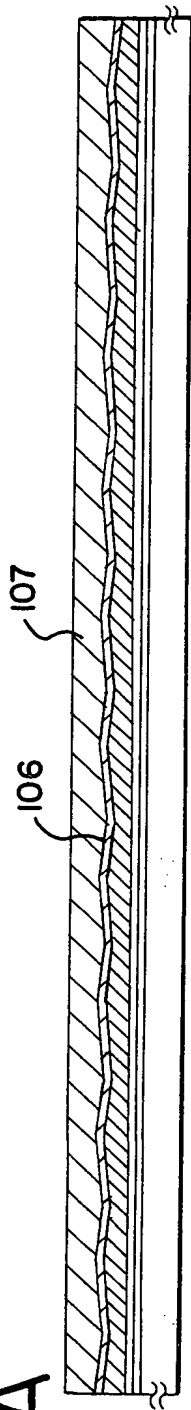
FIG. 1D

LASER LIGHT IRRADIATION



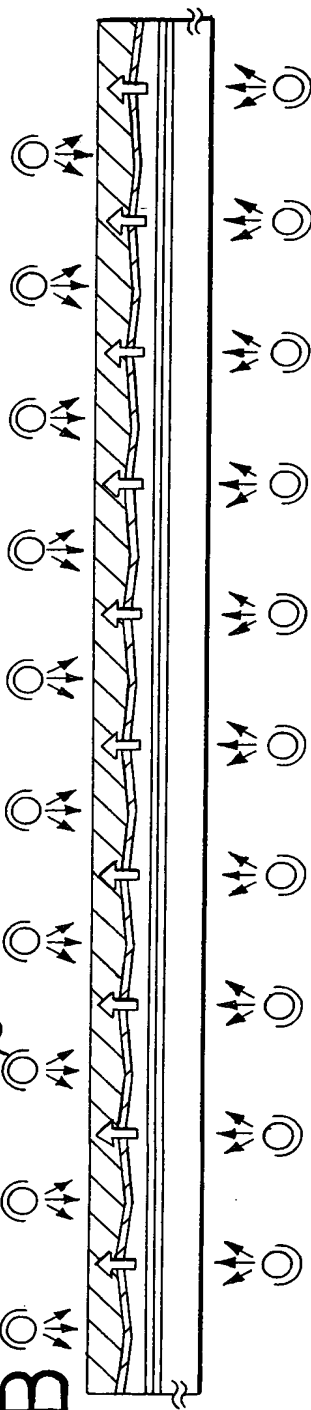
FORMATION OF BARRIER LAYER AND SEMICONDUCTOR FILM CONTAINING RARE GAS ELEMENT

FIG. 2A



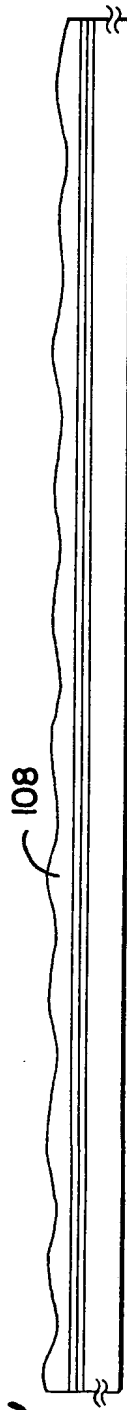
HEAT TREATMENT (GETTERING)

FIG. 2B



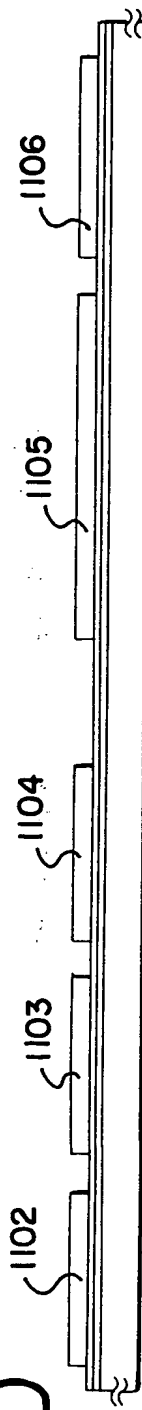
REMOVAL OF BARRIER LAYER AND SEMICONDUCTOR FILM CONTAINING RARE GAS ELEMENT

FIG. 2C



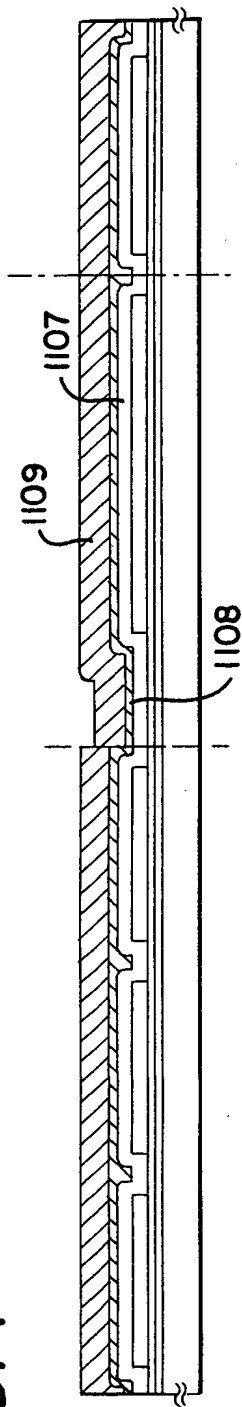
FORMATION OF ACTIVE LAYER

FIG. 2D



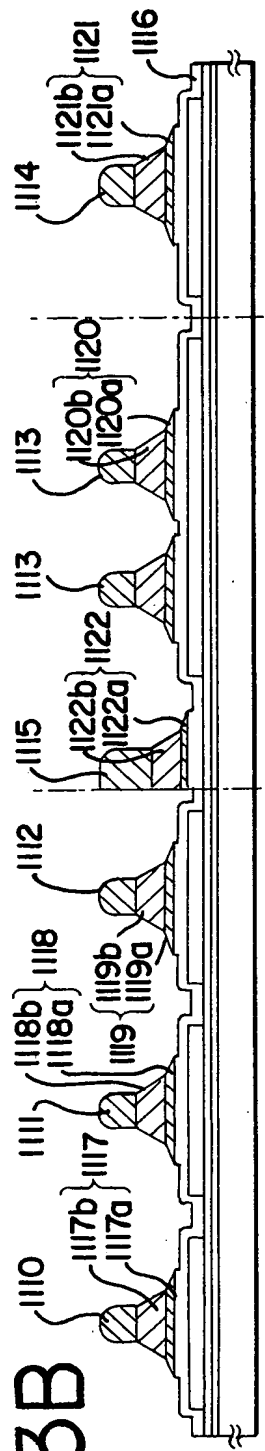
FORMATION OF SEMICONDUCTOR LAYER/FORMATION OF INSULATING FILM/
 FORMATION OF FIRST CONDUCTIVE FILM AND SECOND CONDUCTIVE FILM

FIG. 3A



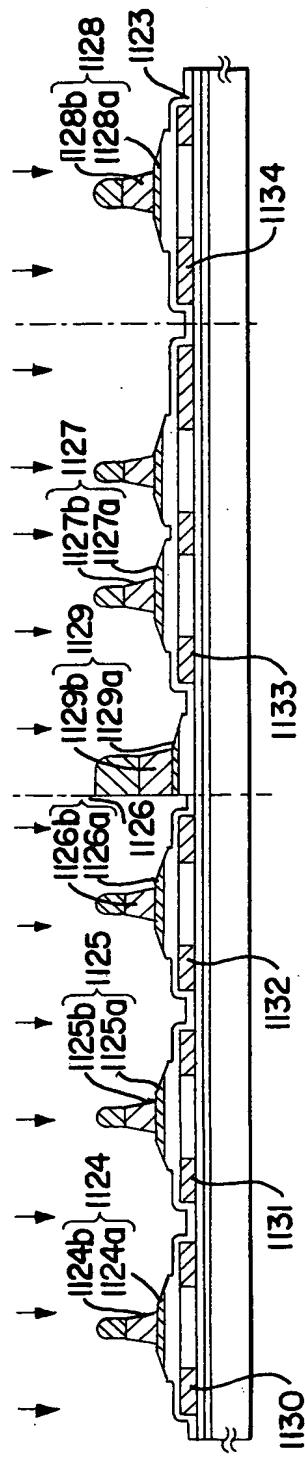
FIRST ETCHING PROCESS

FIG. 3B



SECOND ETCHING PROCESS/
 FIRST DOPING PROCESS

FIG. 3C



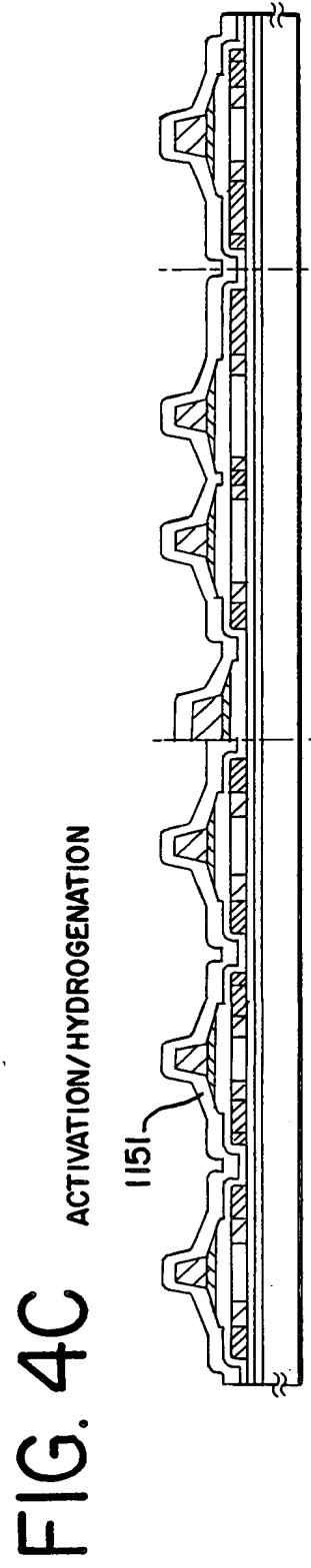
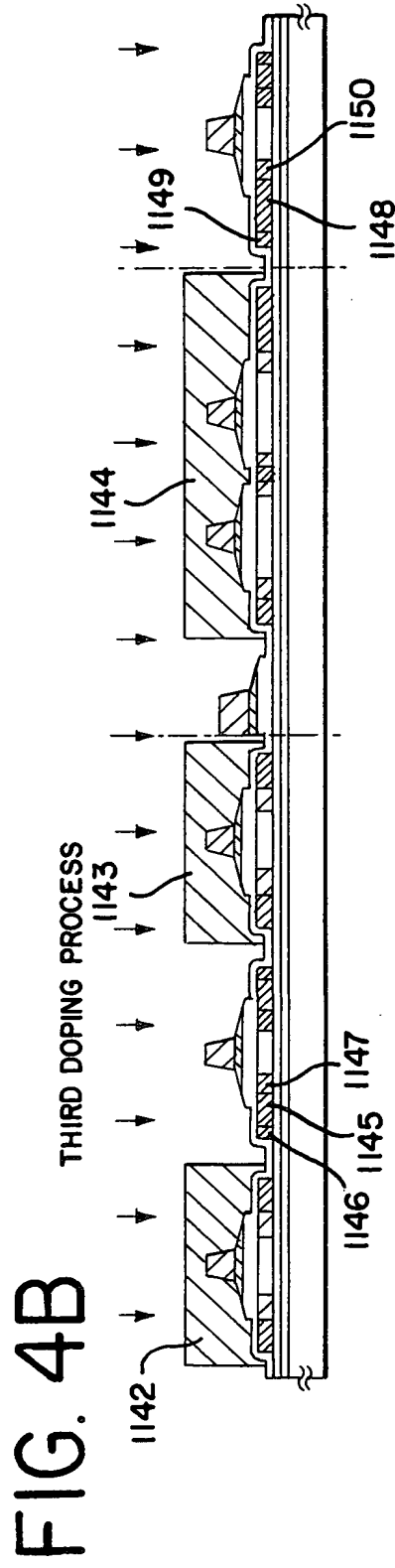
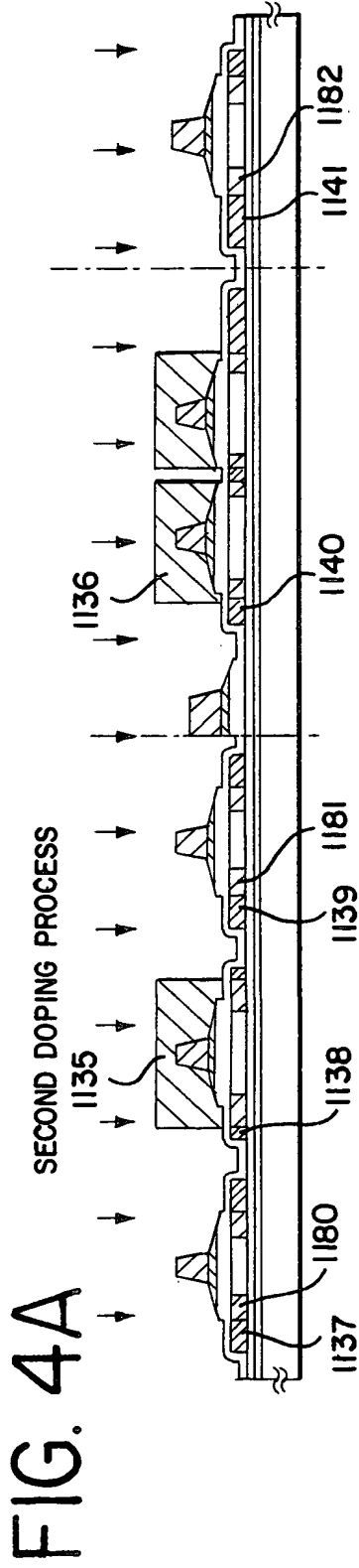


FIG. 5

FORMATION OF INTERPLAYER INSULATING FILM
 FORMATION OF PIXEL ELECTRODE AND WIRING

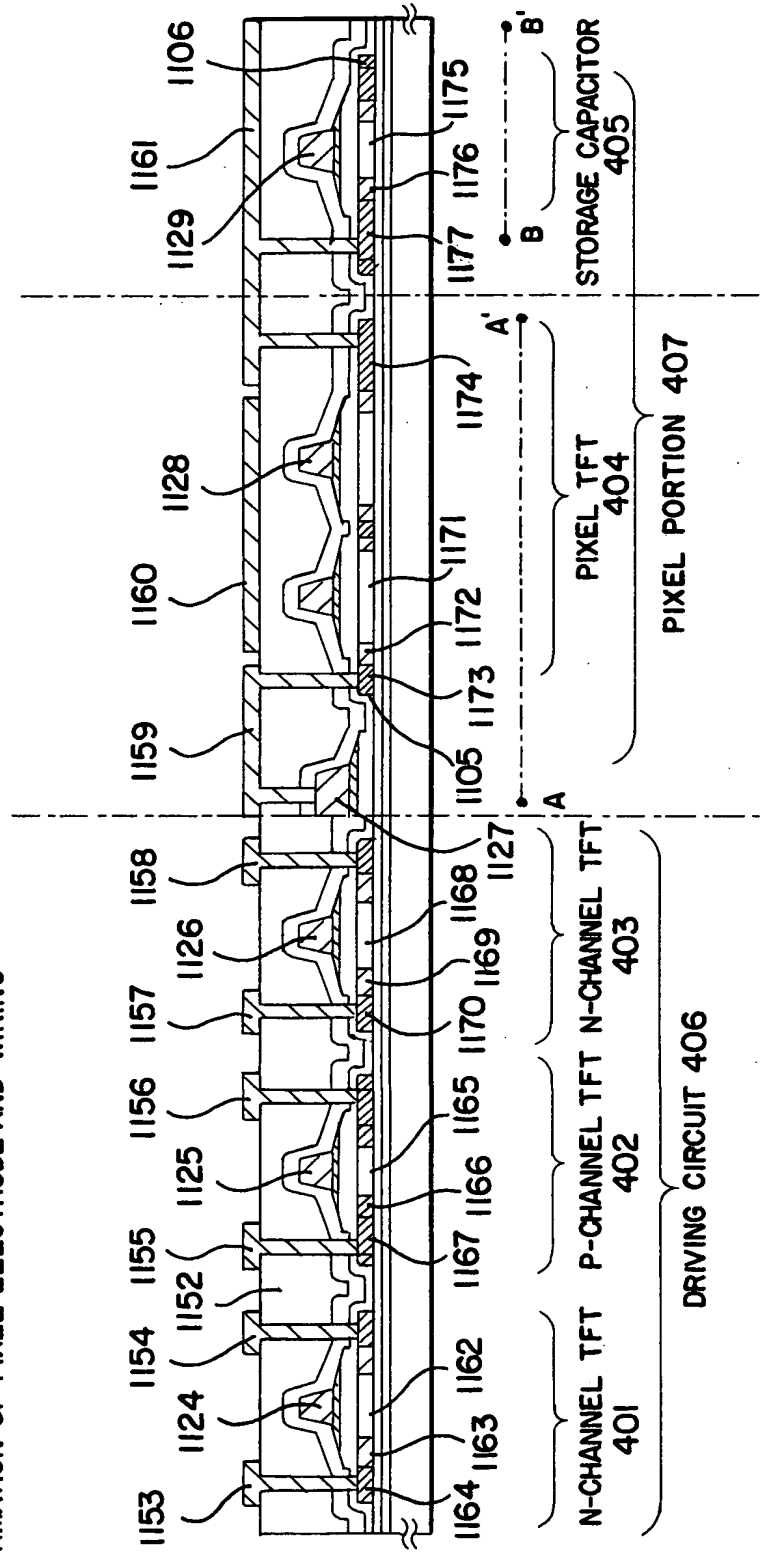


FIG. 6

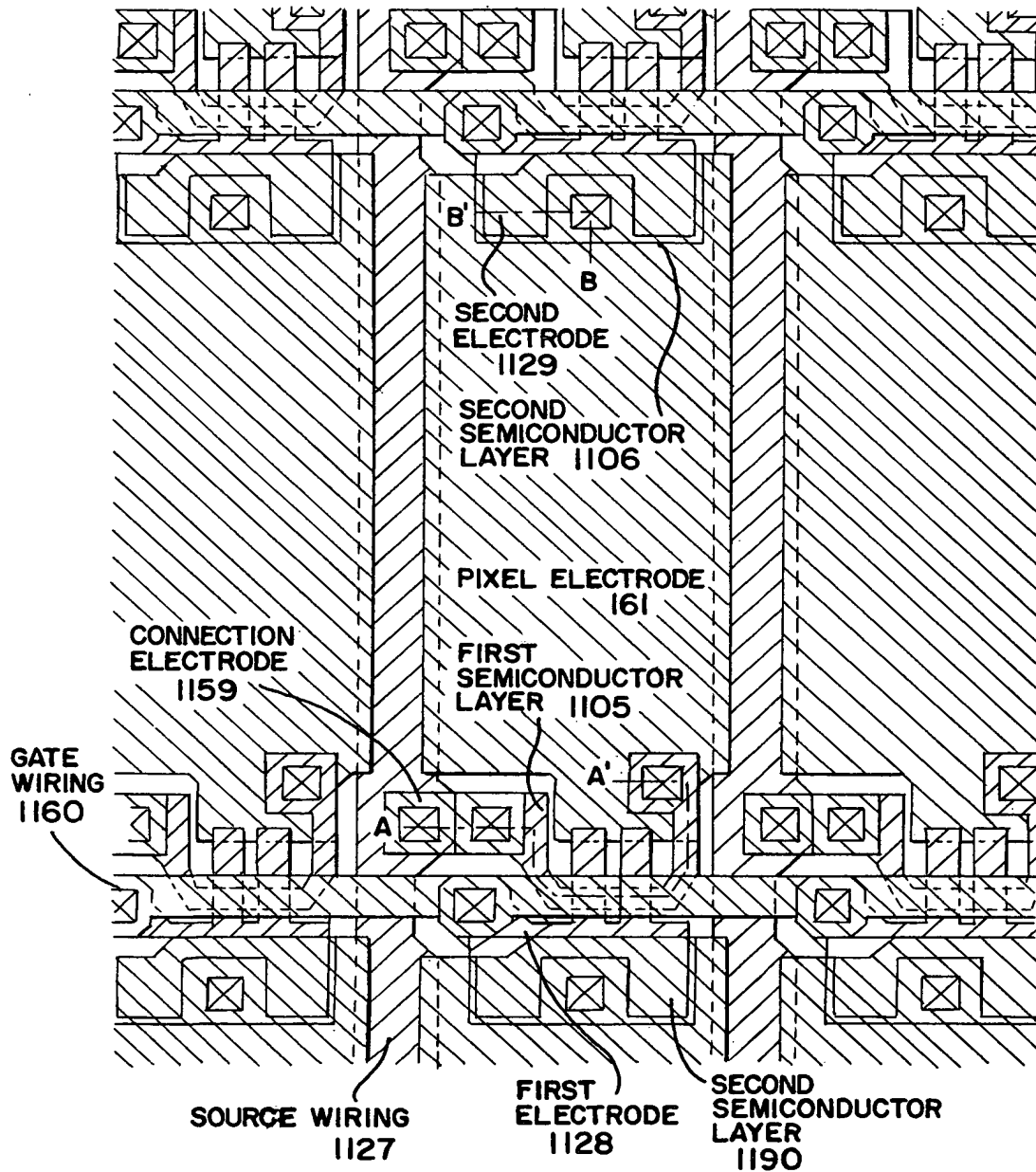


FIG. 7A

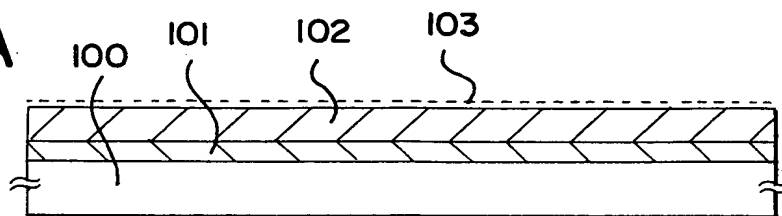


FIG. 7B

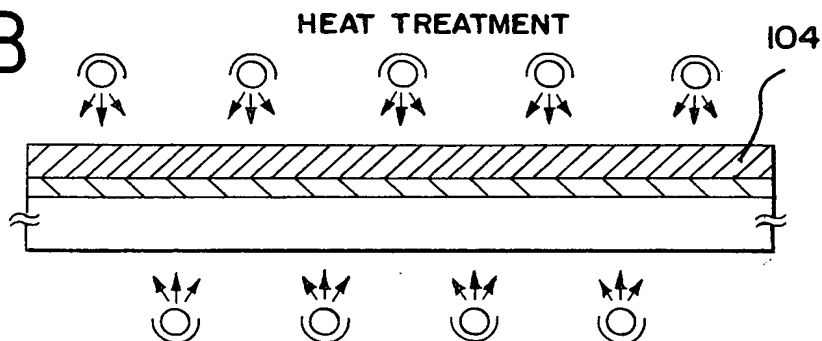


FIG. 7C

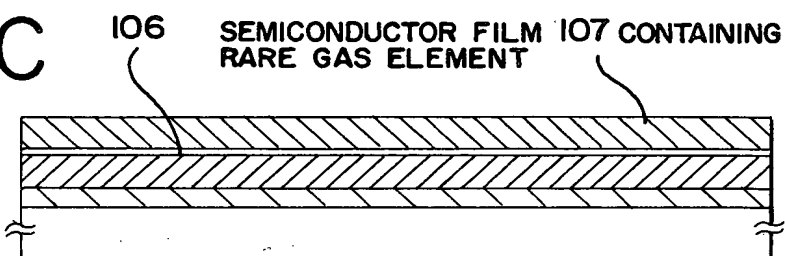


FIG. 7D

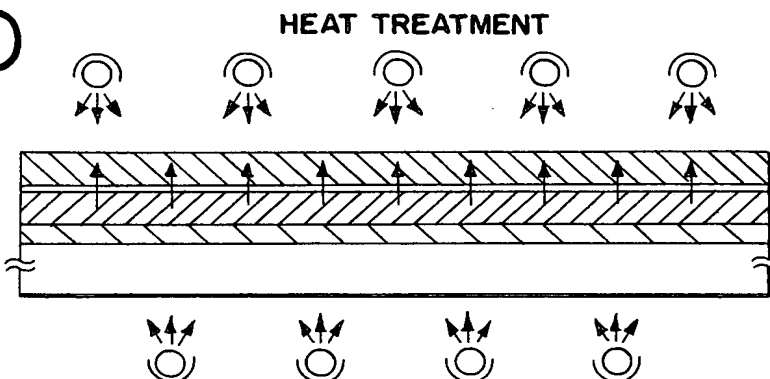


FIG. 7E

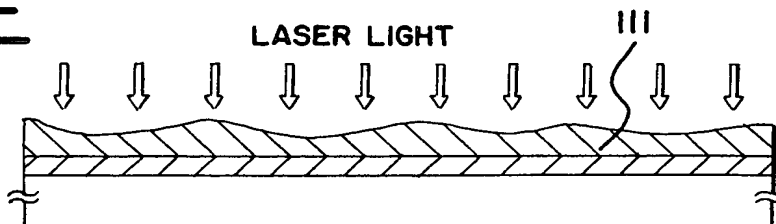


FIG. 8A

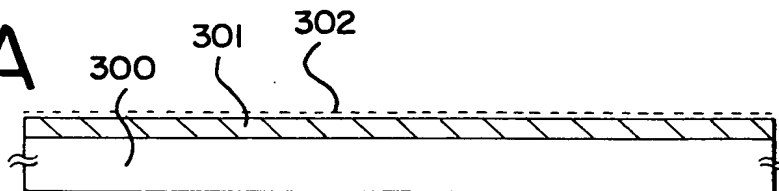


FIG. 8B

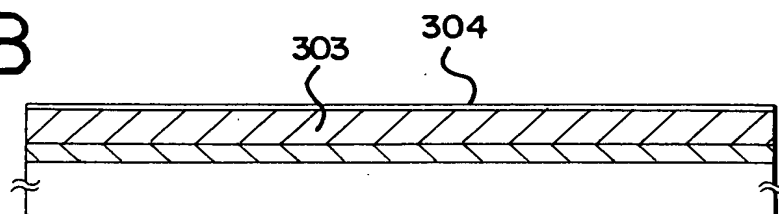


FIG. 8C

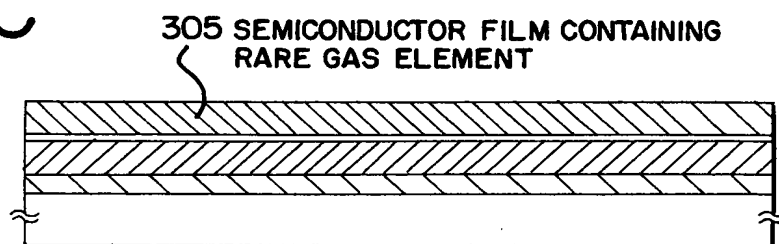


FIG. 8D

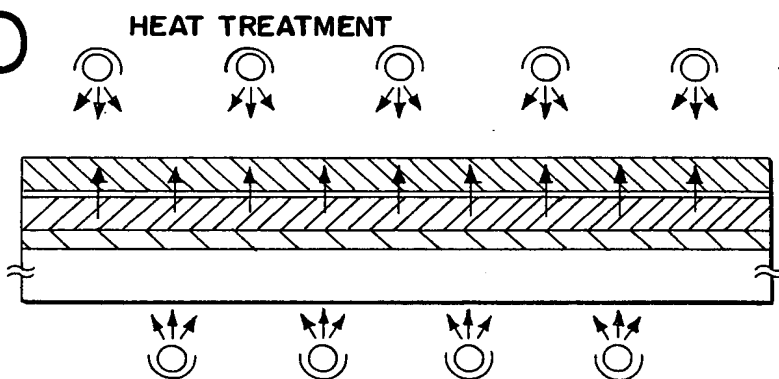


FIG. 8E

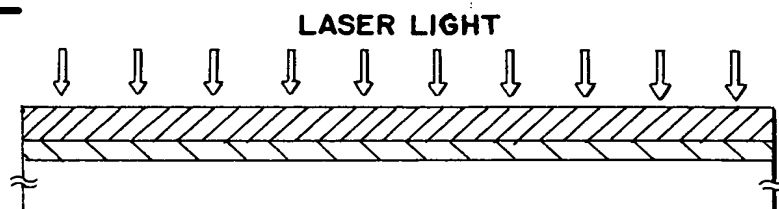




FIG. 9

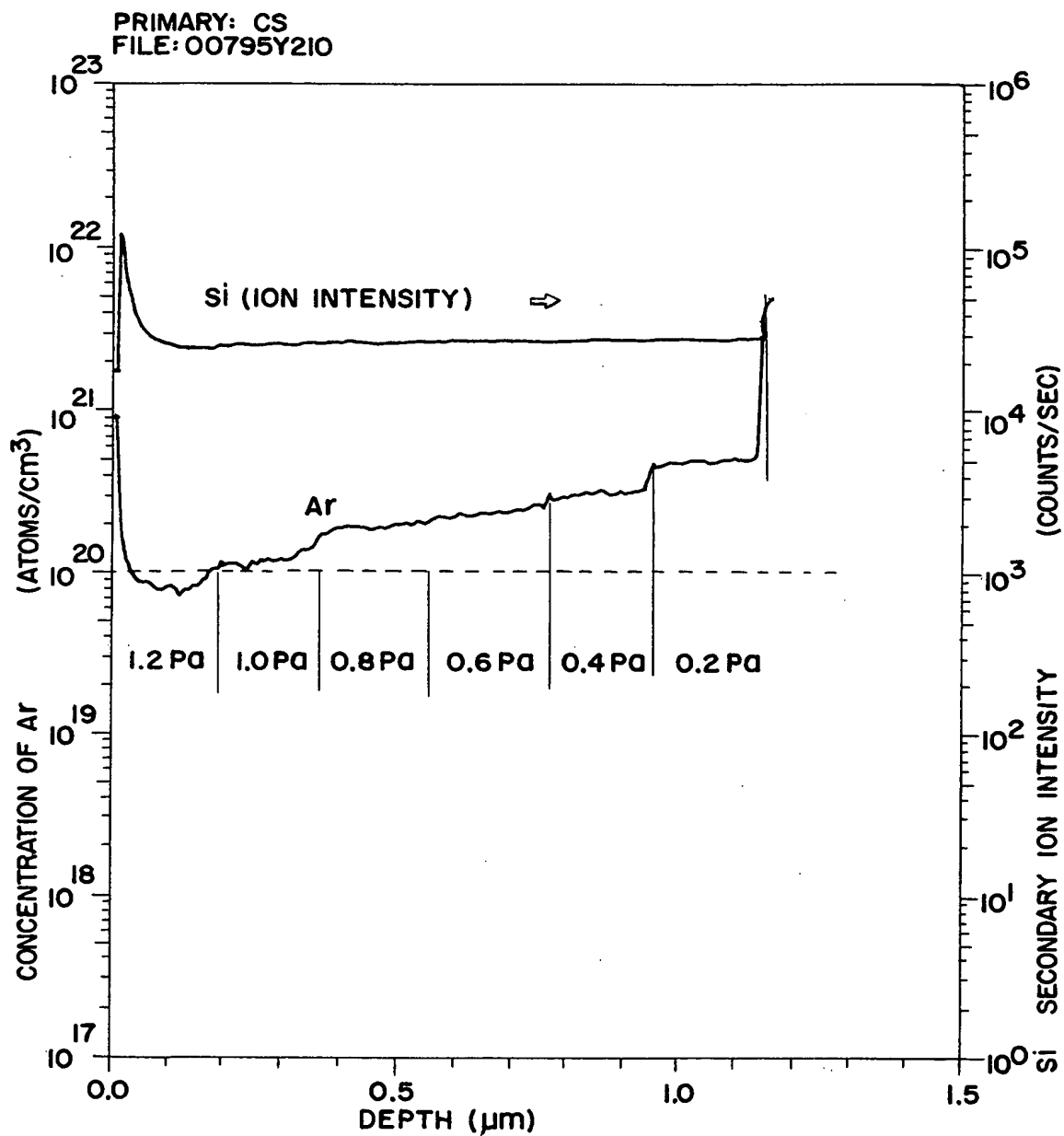


FIG. 10

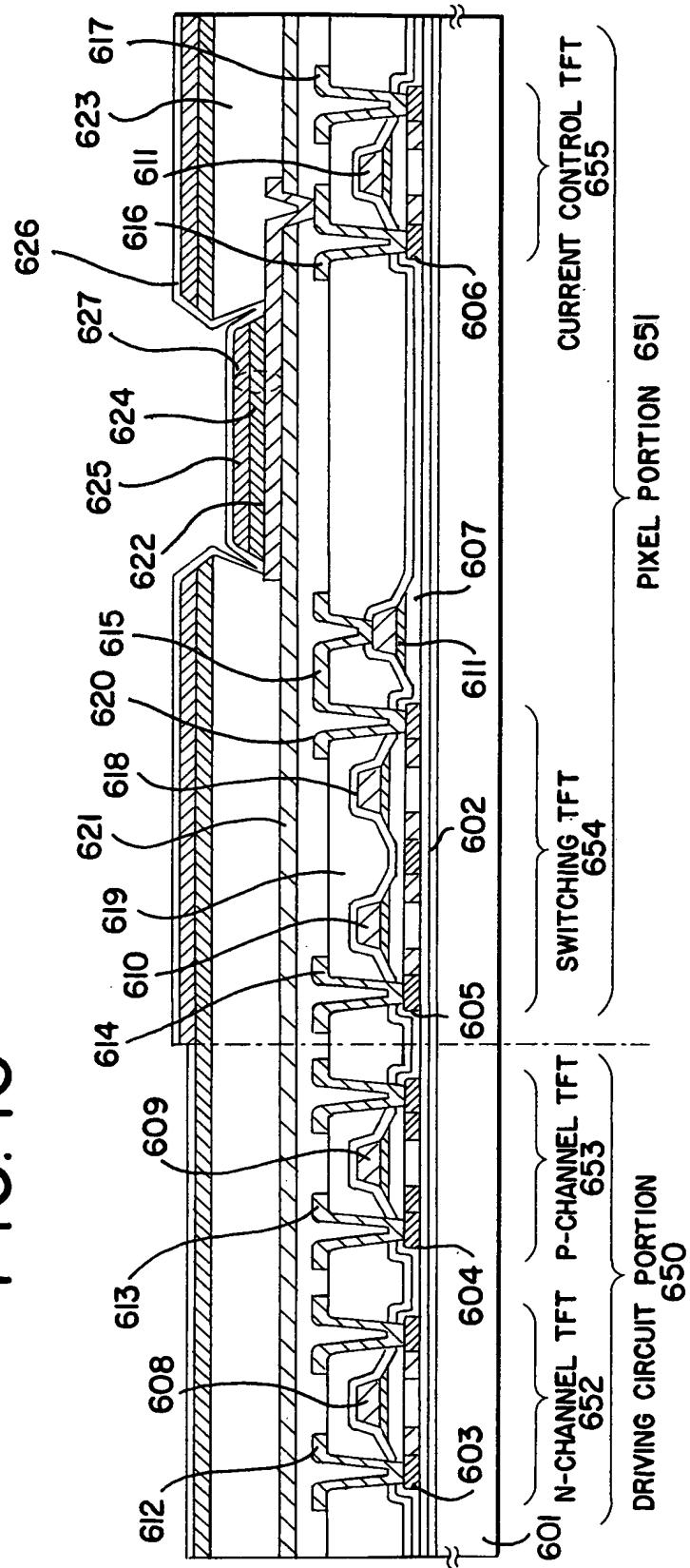




FIG. 11A

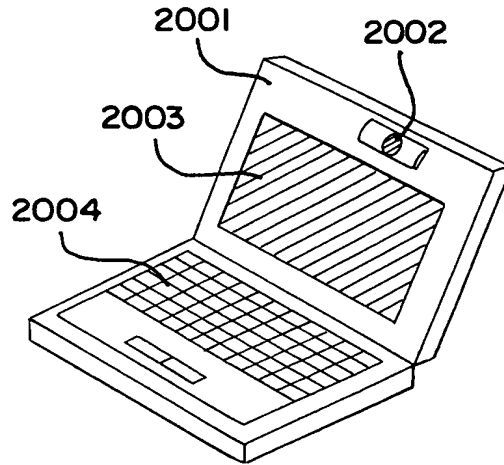


FIG. 11B

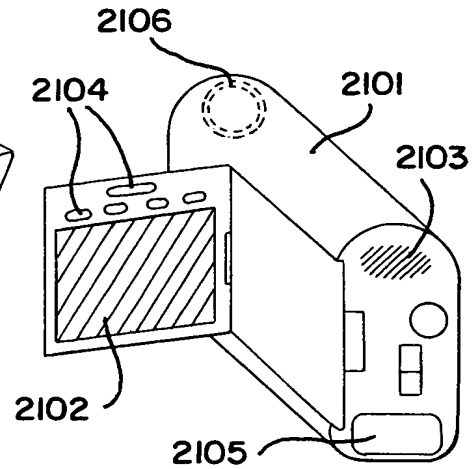


FIG. 11C

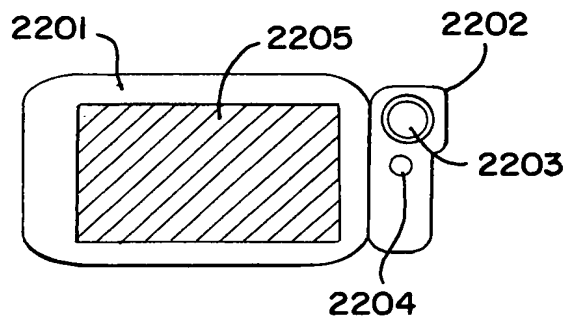


FIG. 11D

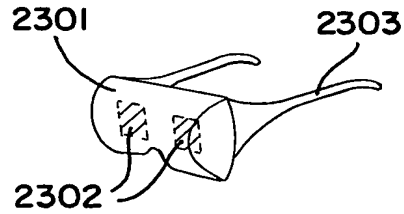


FIG. 11E

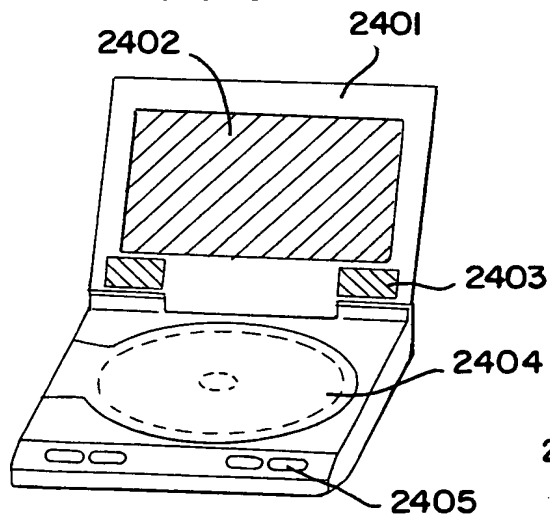


FIG. 11F

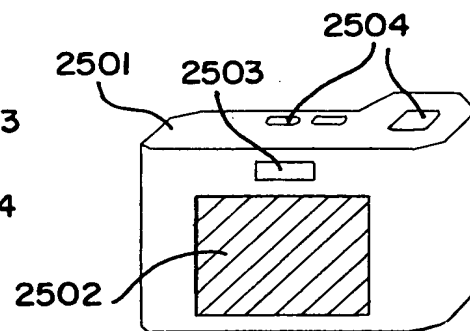


FIG. 12A

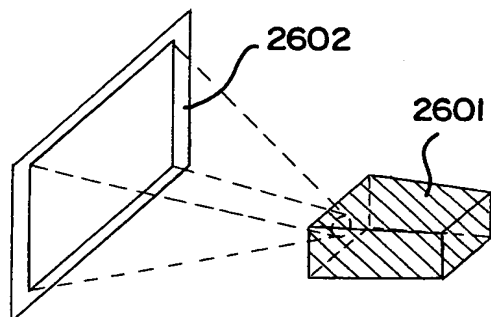


FIG. 12B

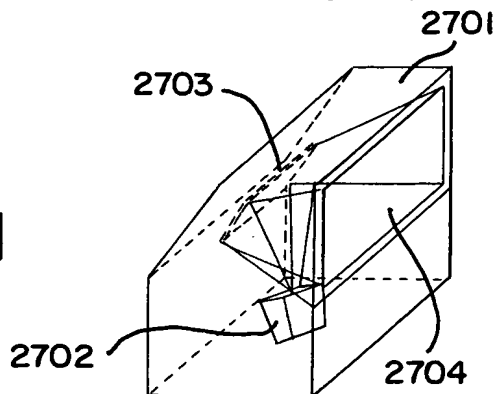


FIG. 12C

PROJECTION APPARATUS
(THREE PLATES TYPE)

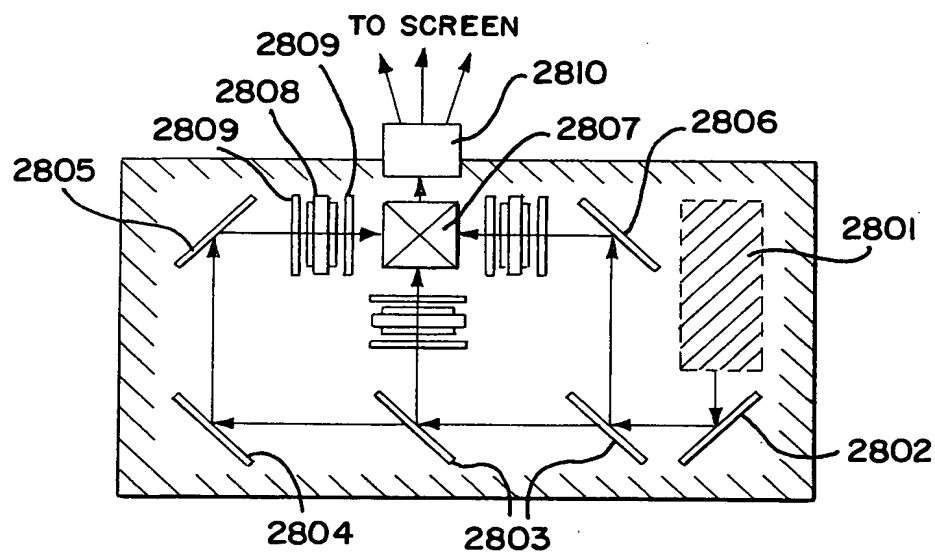


FIG. 12D

LIGHT SOURCE
OPTICAL SYSTEM

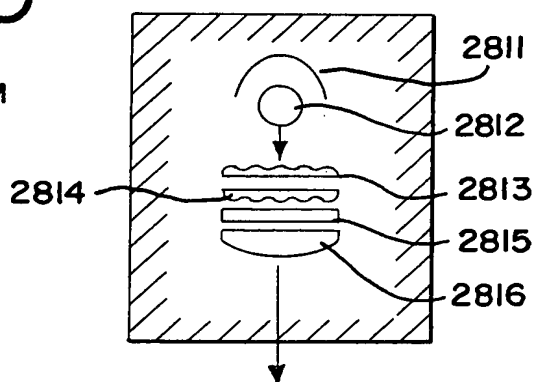




FIG. 13A

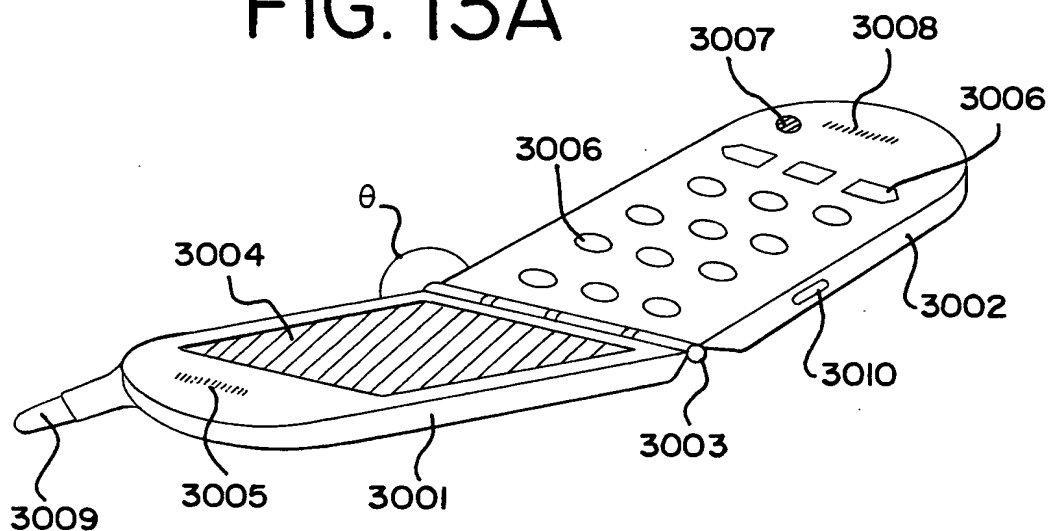


FIG. 13B

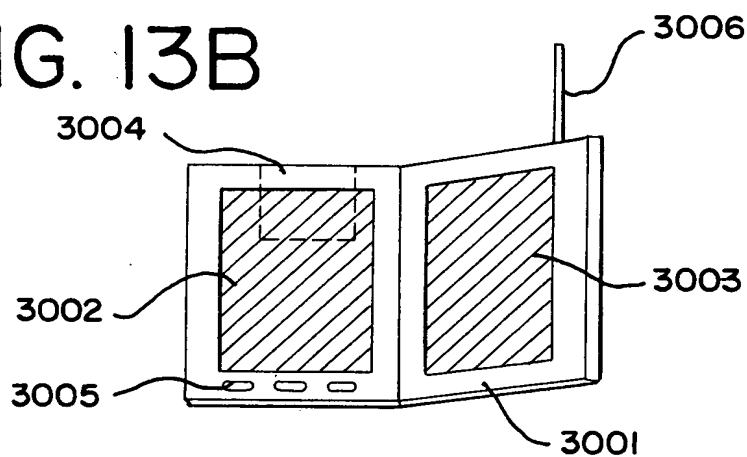


FIG. 13C

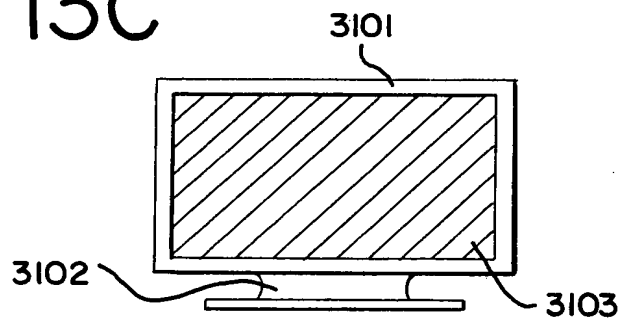


FIG. 14A

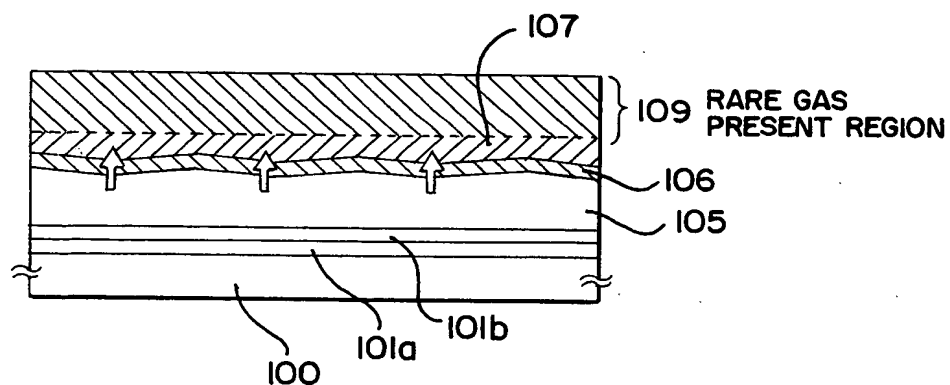


FIG. 14B

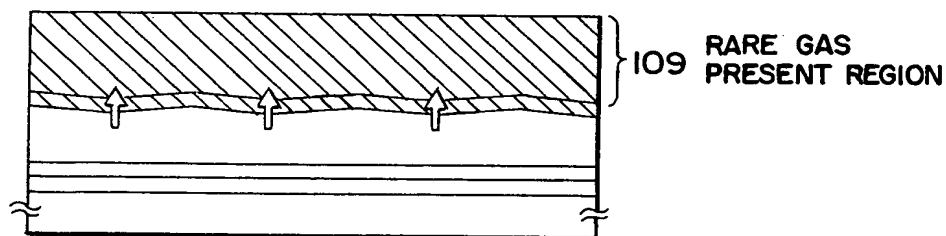


FIG. 14C

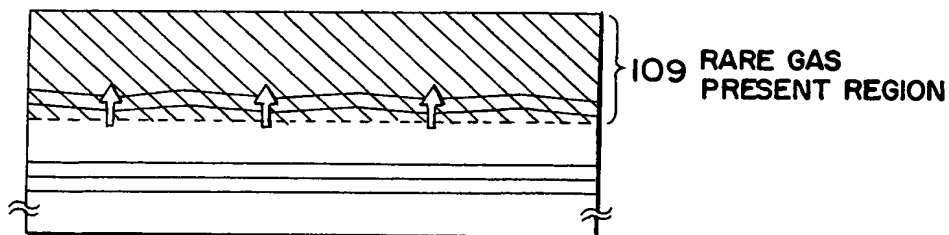


FIG. 15A

FORMATION OF GATE WIRING

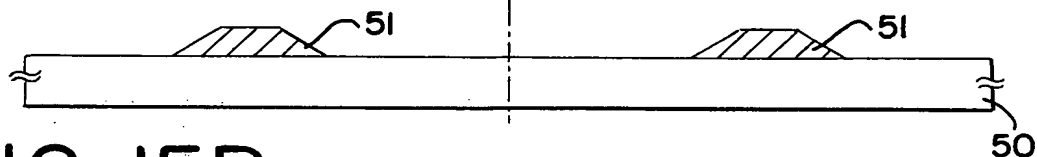


FIG. 15B

FORMATION OF GATE
INSULATING FILM
AND SEMICONDUCTOR FILM

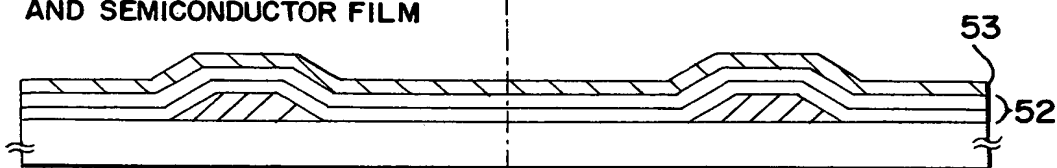


FIG. 15C

CRYSTALLIZATION

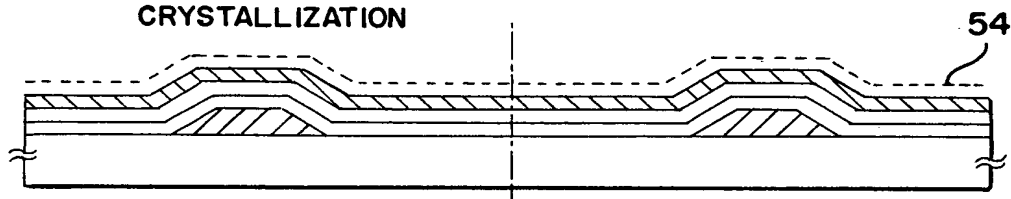


FIG. 15D

GETTERING

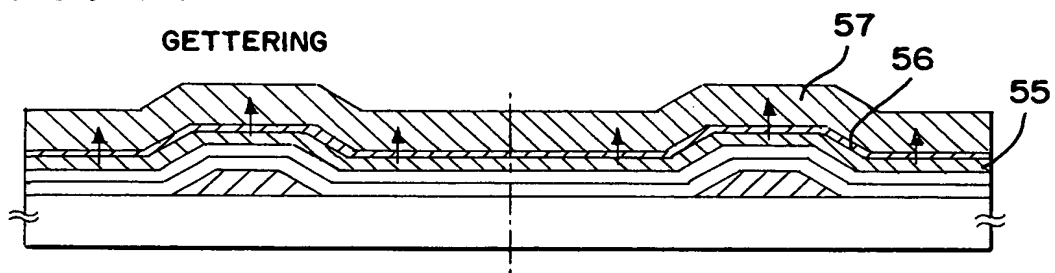


FIG. 15E

ADDITION OF IMPURITY ELEMENT

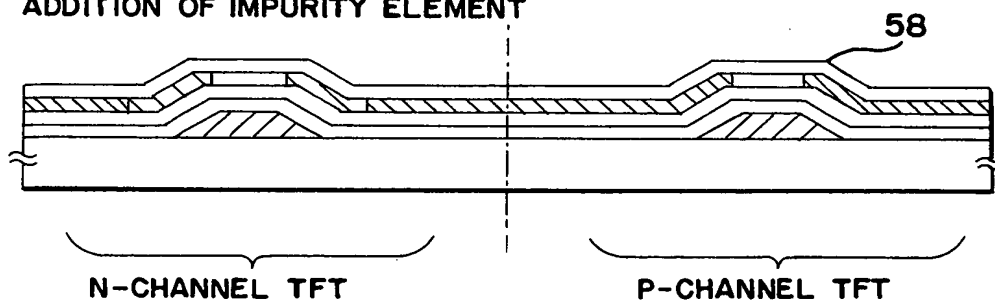




FIG. 16A

ACTIVATION

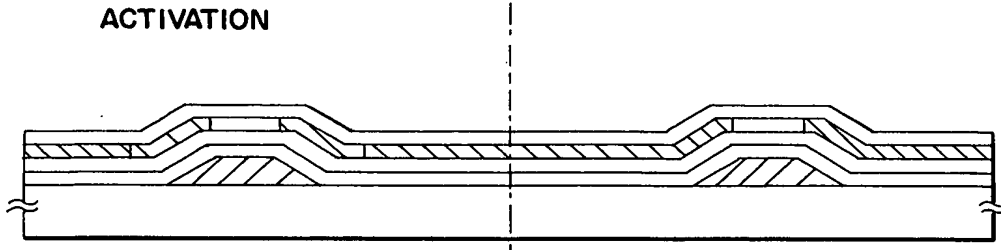


FIG. 16B

FORMATION OF INTERLAYER
INSULATING FILM

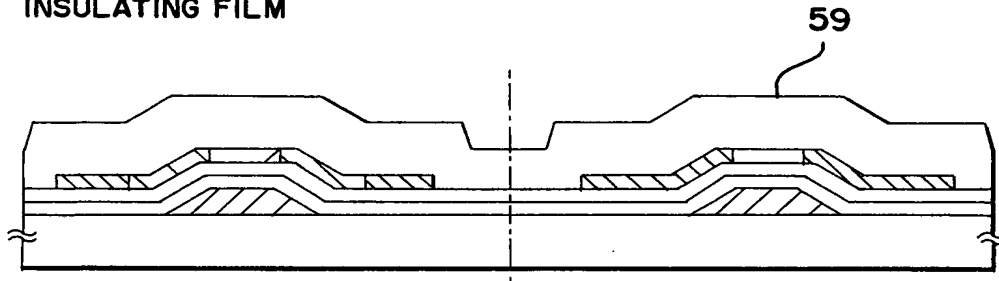


FIG. 16C

FORMATION OF SOURCE WIRING
AND DRAIN WIRING

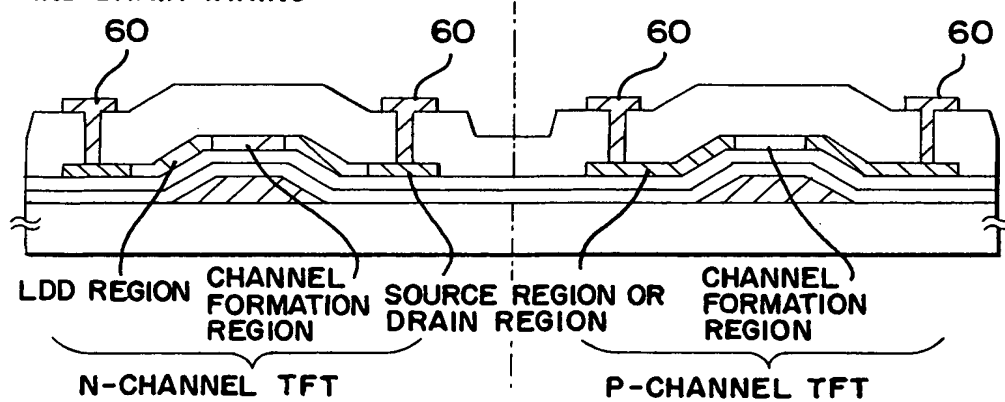


FIG. 17A

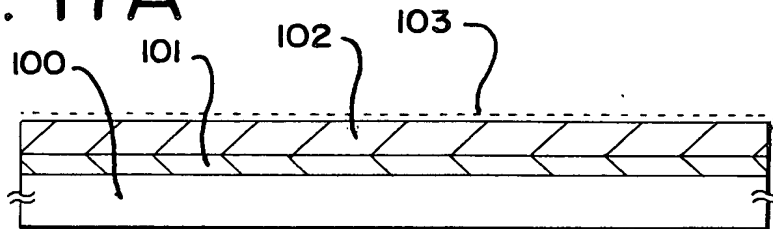


FIG. 17B

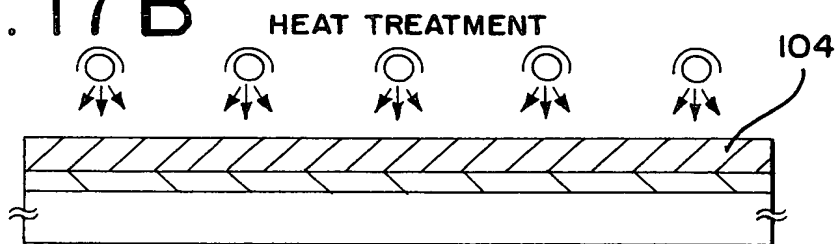


FIG. 17C

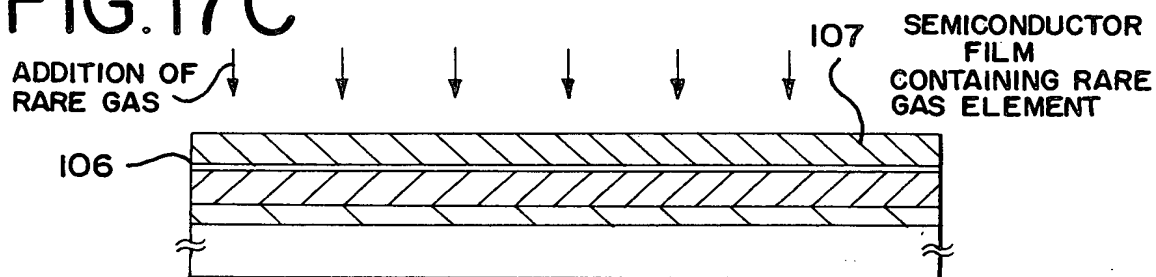


FIG. 17D

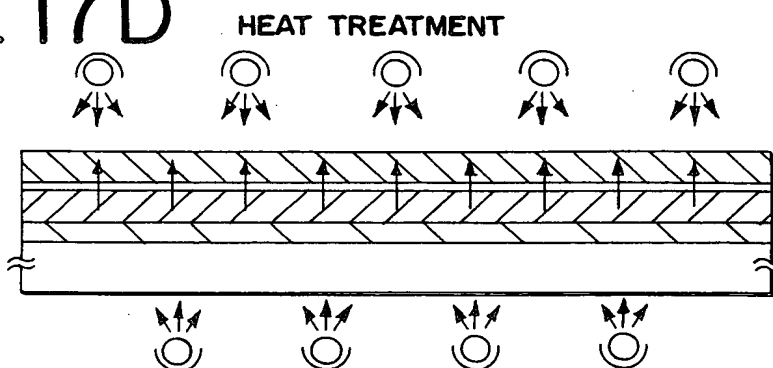


FIG. 17E

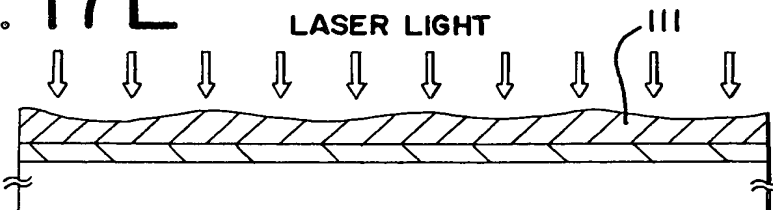


FIG. 18

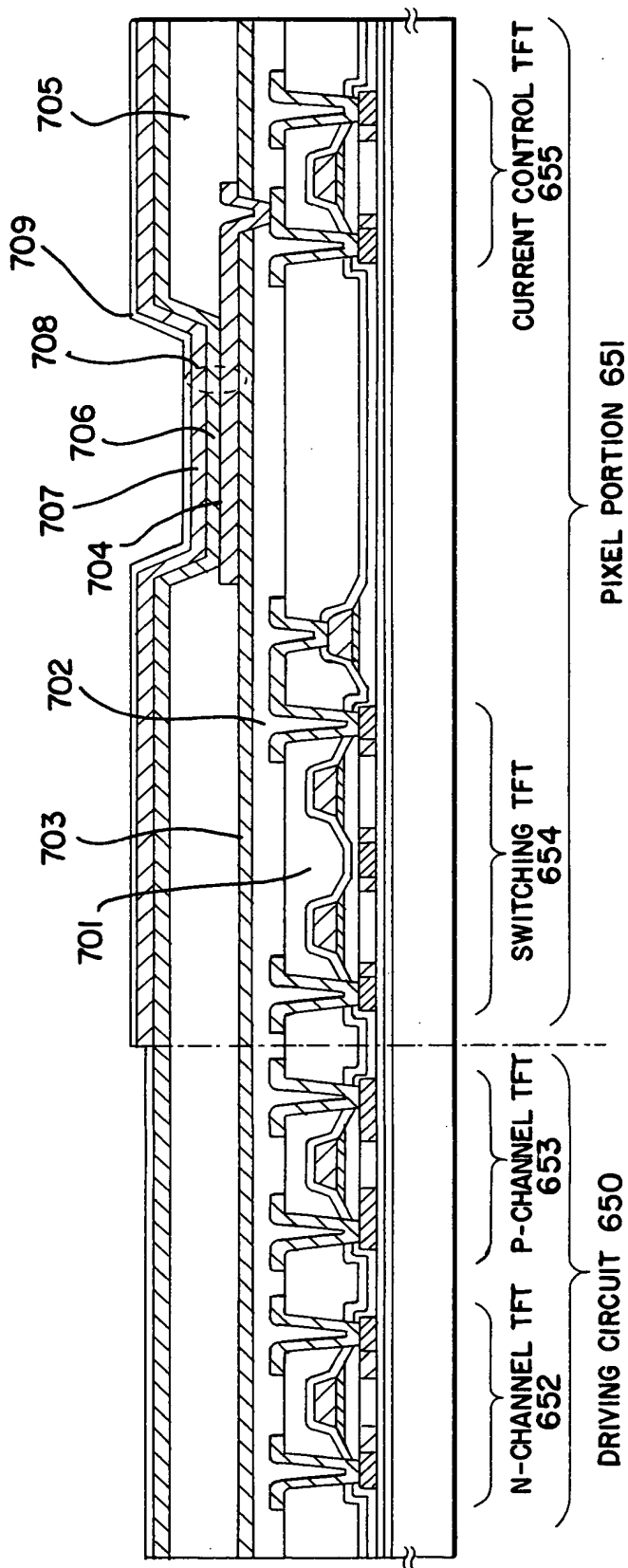
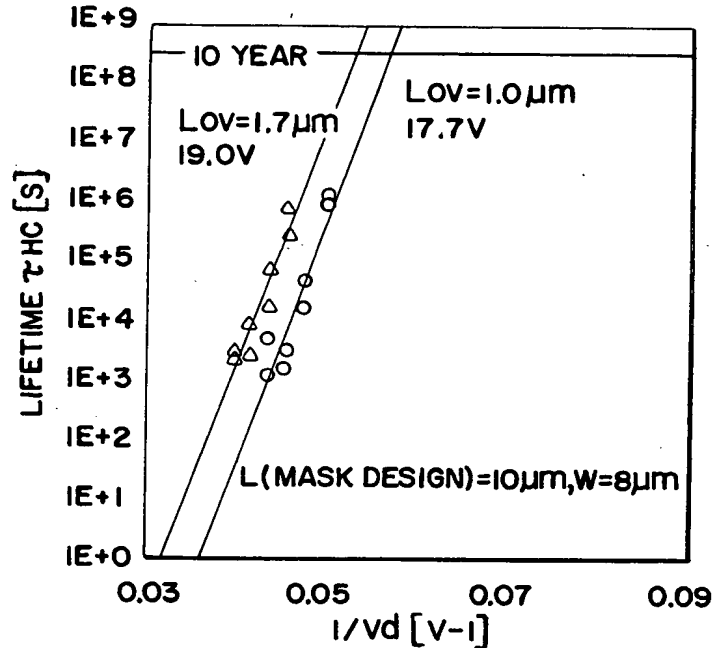
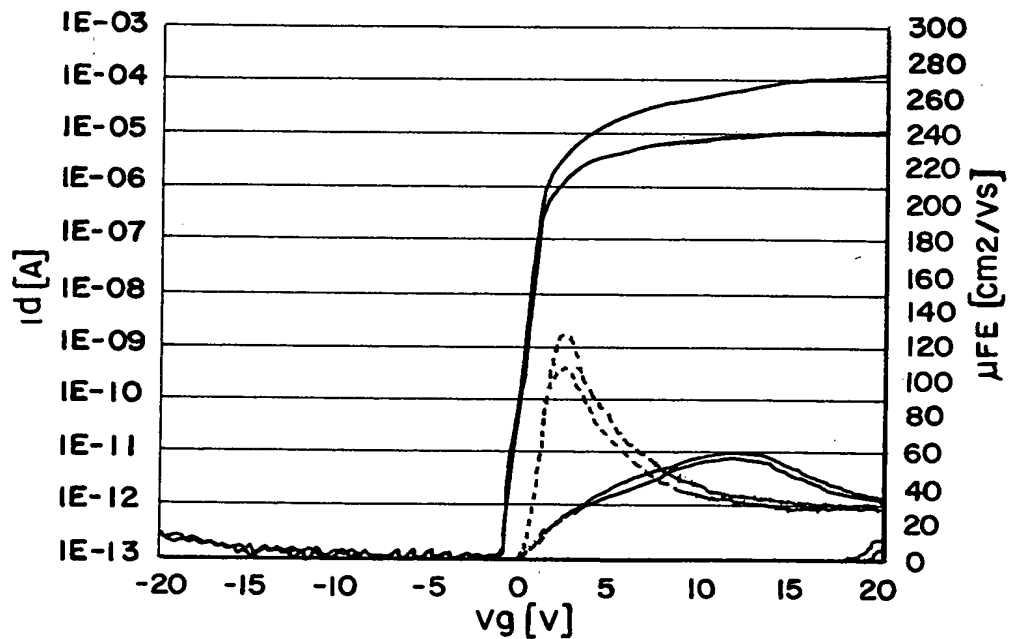


FIG. 19A



ESTIMATED GUARANTEED VOLTAGE (ON CURRENT 10% DEGRADATION)
 DEPENDENCE ON LENGTH OF L_{OV} ($L/W = 10/8 \mu m$)

FIG. 19B



STATIC CHARACTERISTIC OF PIXEL TFT ($L/W = 4.5 \times 2/3 \mu m$)